

ABSTRACT OF THE DISCLOSURE

A layout of a nonvolatile memory structure has multiple memory array banks and multiple double-ended sense amplifiers. Each of the double-ended sense amplifiers is implemented between two of the memory array banks for sharing use, wherein when one array bank is decoded, the other one array bank serving as a reference array. Wherein, every two of the memory array banks are grouped in one dual bank, and one of the double-ended sense amplifiers is implemented in the dual bank. Alternatively, a predetermined number of the memory array banks are grouped into one bank unit for multiple bank units, and one of the double-ended sense amplifiers is implemented between two of the bank units.